

# APPLICATION DATA SHEET

Electronic Version v14

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<b>Title of Invention</b>	METHOD FOR GROWING A GATE OXIDE LAYER ON A SILICON SURFACE WITH PRELIMINARY N <sub>2</sub> O ANNEAL
Application Type :	regular, utility
Attorney Docket Number :	NTCP0014USA
Correspondence address:	
Customer Number:	027765
	
Priority Data:	
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